PUBLISHER CORRECTION OPEN

Publisher Correction: Ambipolar device simulation based on the drift-diffusion model in ion-gated transition metal dichalcogenide transistors

Akiko Ueda , Yijin Zhang , Nobuyuki Sano, Hiroshi Imamura and Yoshihiro Iwasa

npj Computational Materials (2020)6:37; <https://doi.org/10.1038/s41524-020-0314-9>

Correction to: *npj Computational Materials* <https://doi.org/10.1038/s41524-020-0293-x>, published online 20 March 2020

The original version of this Article contained an error in the spelling of the last word of the Title. This error has been corrected in both the PDF and HTML versions of the Article.

Open Access This article is licensed under a Creative Commons Attribution 4.0 International License, which permits use, sharing, adaptation, distribution and reproduction in any medium or format, as long as you give

appropriate credit to the original author(s) and the source, provide a link to the Creative Commons license, and indicate if changes were made. The images or other third party material in this article are included in the article's Creative Commons license, unless indicated otherwise in a credit line to the material. If material is not included in the article's Creative Commons license and your intended use is not permitted by statutory regulation or exceeds the permitted use, you will need to obtain permission directly from the copyright holder. To view a copy of this license, visit <http://creativecommons.org/licenses/by/4.0/>.

© The Author(s) 2020